

## ABSTRACT

The refractive index of the material for forming a light emitting element, example of the material including a group III Nitride Compound Semiconductor, is relatively higher than that of air; therefore, in order to emit, into air, light generated in an active layer in conventional semiconductor light emitting devices, it is indispensable that its incidence angle from their semiconductor layer into the air is the critical angle of total reflection or less. If the incidence angle is more than the critical angle of total reflection, the light cannot go out into the air, and is totally reflected. In order to solve the problem, the invention is a semiconductor light emitting device including a substrate, and at least a first semiconductor layer, an active layer and a second semiconductor layer that are sequentially provided on the substrate, wherein the second semiconductor layer has a polarity different from that of the first semiconductor layer, and the total area of the first semiconductor layer, the active layer and the second semiconductor layer in side faces where the active layer is uncovered is 5% or more of the area of the upper face which is uncovered at the side of the second semiconductor layer.